风光欣技术资料

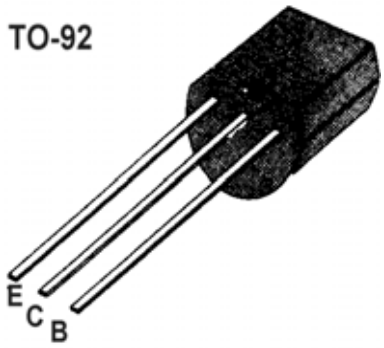
A1297

—PNP silicon —

■■**APPLICATION:**Power Amplifier Application, Power Switching Application.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE}	120		400		V_{CE}= -2V，Ic= -100mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -20V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -6V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-20			V	Ic= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-20			V	Ic= -10mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-6			V	I_E= -0.1mA，Ic=0
Base-Emitter Voltage	V_{BE}			-0.85	V	V_{CE}= -2V，Ic= -100mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	Ic= -2A，I_B= -100mA
Gain bandwidth product	f_T		120		MHz	Ic= -500mA，V_{CE}= -2V
Common Base Output Capacitance	Cob		40		PF	V_{CB}= -10V，I_E=0，f = 1MHz

■■h_{FE} **Classification**

Classification	Y	GR
h_{FE}	120~240	200~400